

B' an electrical isolation region disposed in the semiconductor substrate between the first region and the second region.

B<sup>2</sup> 12. (Amended) An ESD protection structure formed in a semiconductor material of a first conductivity type, the structure comprising:  
a well region of a second conductivity type formed in the semiconductor material, the well region having a floating potential;  
a first region of the first conductivity type formed in the well region;  
a second region of the second conductivity type formed in the semiconductor material and spaced apart from the first region and the well; and  
an electrical isolation region formed in the semiconductor material between the first region and the second region.

Please add the following new claims:

B<sup>3</sup> --15. An ESD protection structure formed in a semiconductor material of a first conductivity type, the structure comprising:  
an isolation region formed in the semiconductor material;  
a first region of a second conductivity type formed in the semiconductor material, the first region having a dopant concentration;  
a well region of the second conductivity type formed in the semiconductor material, the well region contacting the isolation region, being spaced apart from the first region, having a dopant concentration that is less than the dopant concentration of the first region, and not contacting a region of the second conductivity type that has a dopant concentration that is greater than the dopant concentration of the well region; and  
a second region of the first conductivity type formed in the well region, the second region contacting the isolation region and having a dopant concentration.

SUB C1 16. The structure of claim 15 wherein the semiconductor material has a dopant concentration that is less than the dopant concentration of the second region.

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PATENT

AMENDMENT IN RESPONSE TO  
(OFFICE ACTION DATED MAY 30, 2002)

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17. The structure of claim 15 wherein the second region is connected to an  
electrical pad.

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18. The structure of claim 17 wherein the first region is connected to ground.--